

In the Specification:

Please amend the paragraph on page 6, line 28 (Par. [0042] as published):

FIG. 10 shows diagrammatically a cross-sectional view of a device of the invention, in which the free-standing film 30, 220 is part of a MEMS element 10. The device further comprises a thin film capacitor 50 and a vertical interconnect 60. The device is present on top of a substrate 14, which comprises in this case a body 141 of Si and a thermal oxide surface 142. This Figure illustrates an advantageous embodiment in which the MEMS element having three electrodes 20, 30, 220 can be embedded in a passive network that comprises other components as well, and without the need to apply any additional metal layer, or sacrificial layer. In fact, the first sacrificial layer 16 functions also as a dielectric of the thin-film capacitor 50. The electrodes 20, 220, 30 are mutually separated by an air gap 26. The electrodes 51,52 of the thin-film capacitor 50 are defined in the same metal layers as the second and the third electrode of the MEMS element 10. The mechanical layer 12 is not only second electrode 30, but also interconnect. It is herein of particular importance for the first and second sacrificial layers 16, 17 to be selectively etched away. It is therewith improved in that not just one aperture in the mechanical layer 12 is present, but a plurality of apertures; and in that the supporting structure has a substantial extension, i.e. it is primarily wall-shaped and not pillar-shaped.